

SIPMOS® Power-Transistor

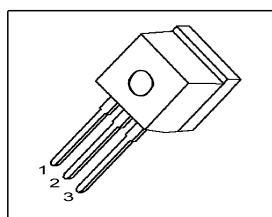
Feature

- N-Channel
- Enhancement mode
- 175°C operating temperature
- Avalanche rated
- dv/dt rated
- Green package (lead free)

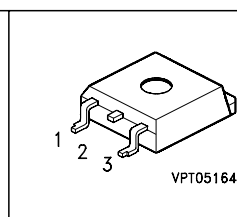
Product Summary

V_{DS}	100	V
$R_{DS(on)}$	33	mΩ
I_D	47	A

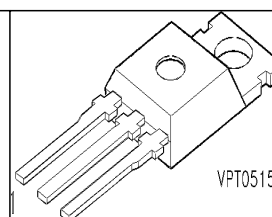
P-TO262-3-1



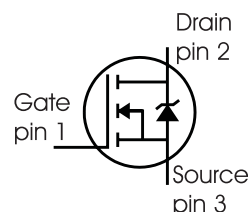
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
IPP47N10S-33	PG-TO220-3-1	SP0002-25706	N1033
IPB47N10S-33	PG-TO263-3-2	SP0002-25702	N1033
IPI47N10S-33	PG-TO262-3-1	SP0002-25703	N1033



Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D		A
$T_C = 25^\circ\text{C}$		47	
$T_C = 100^\circ\text{C}$		33	
Pulsed drain current	$I_{D \text{ puls}}$	188	
$T_C = 25^\circ\text{C}$			
Avalanche energy, single pulse	E_{AS}	400	mJ
$I_D = 47 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_{GS} = 25 \Omega$			
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	17.5	
Reverse diode dv/dt	dv/dt	6	kV/μs
$I_S = 47 \text{ A}$, $V_{DS} = 0 \text{ V}$, di/dt = 200 A/μs			
Gate source voltage	V_{GS}	±20	V
Power dissipation	P_{tot}	175	W
$T_C = 25^\circ\text{C}$			
Operating and storage temperature	T_j , T_{stg}	-55... +175	°C
IEC climatic category; DIN IEC 68-1		55/175/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.85	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	62	
@ 6 cm ² cooling area ¹⁾		-	-	40	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=2mA$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 2\text{ mA}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS}=100V, V_{GS}=0V, T_j=25^{\circ}C$ $V_{DS}=100V, V_{GS}=0V, T_j=150^{\circ}C$	I_{DSS}	-	0.1	1	μA
		-	-	100	
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	10	100	nA
Drain-source on-state resistance $V_{GS}=10V, I_D=33A$	$R_{DS(on)}$	-	25	33	m Ω

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 33\text{A}$	13	26	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	2000	2500	pF
Output capacitance	C_{oss}		-	370	465	
Reverse transfer capacitance	C_{rss}		-	190	240	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 47\text{A}$, $R_G = 4.7\Omega$	-	25	39	ns
Rise time	t_r		-	23	36	
Turn-off delay time	$t_{d(off)}$		-	63	99	
Fall time	t_f		-	15	22.5	

Gate Charge Characteristics

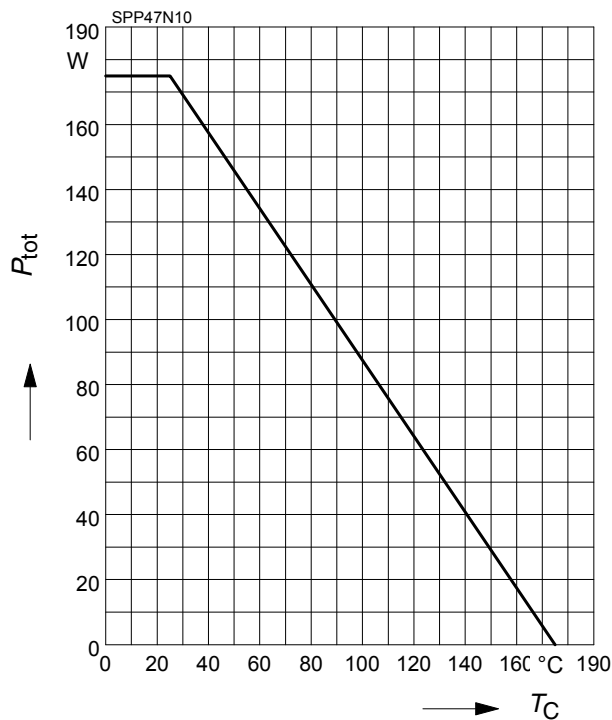
Gate to source charge	Q_{gs}	$V_{DD} = 80\text{V}$, $I_D = 47\text{A}$	-	19	28.5	nC
Gate to drain charge	Q_{gd}		-	29	43.5	
Gate charge total	Q_g	$V_{DD} = 80\text{V}$, $I_D = 47\text{A}$, $V_{GS} = 0 \text{ to } 10\text{V}$	-	70	105	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 80\text{V}$, $I_D = 47\text{A}$	-	6.03	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_C = 25^\circ\text{C}$	-	-	47	A
Inverse diode direct current, pulsed	I_{SM}		-	-	188	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = 94\text{A}$	-	1.1	1.5	V
Reverse recovery time	t_{rr}	$V_R = 50\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	100	150	ns
Reverse recovery charge	Q_{rr}		-	400	600	nC

1 Power dissipation

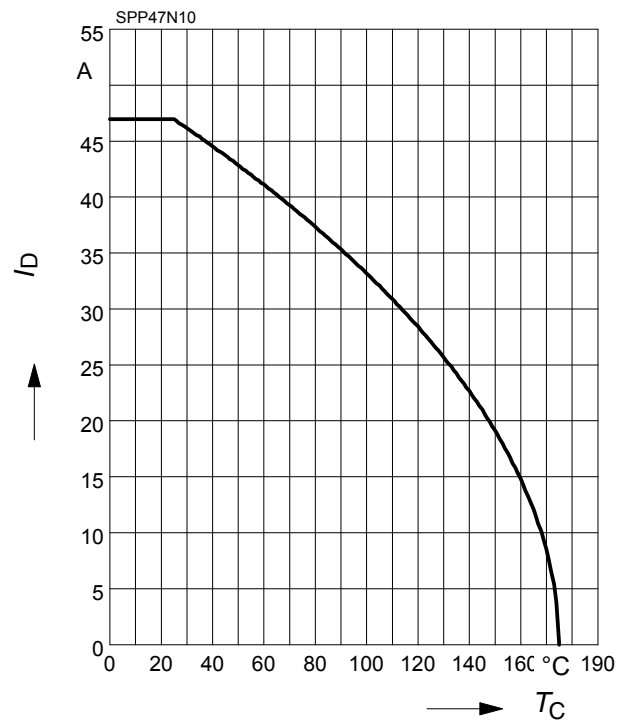
$$P_{\text{tot}} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

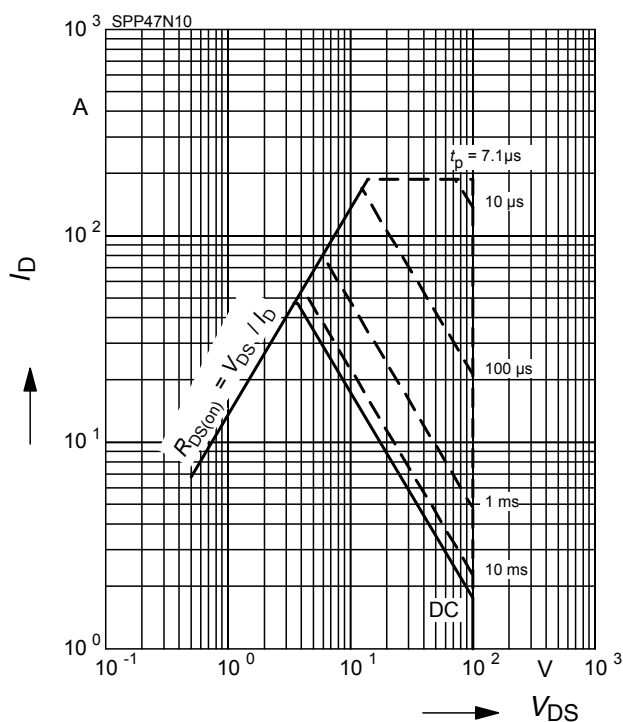
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

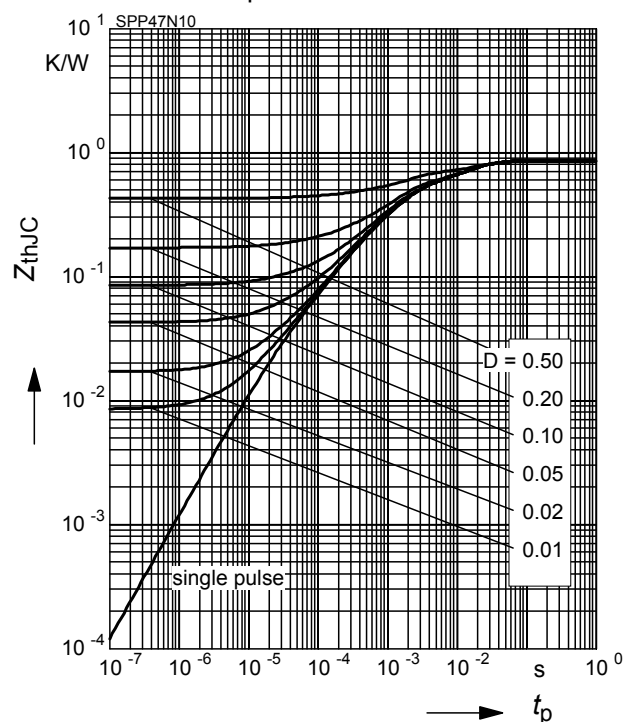
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



4 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

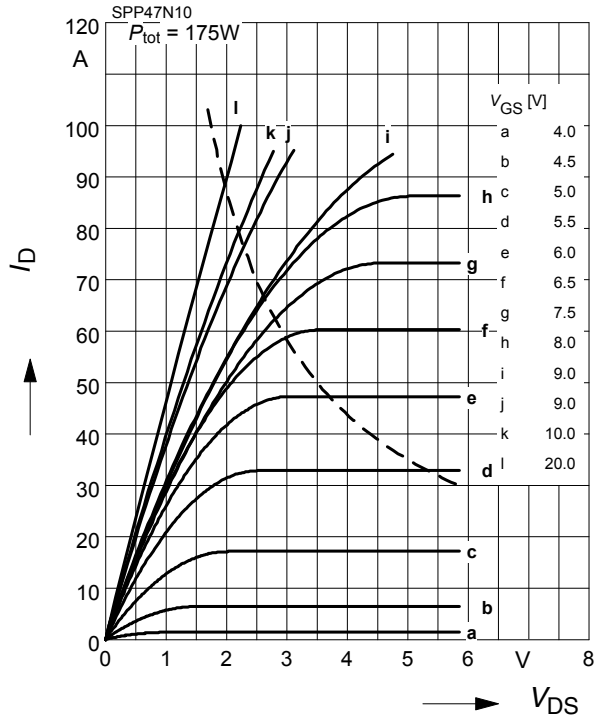
parameter: $D = t_p / T$



5 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

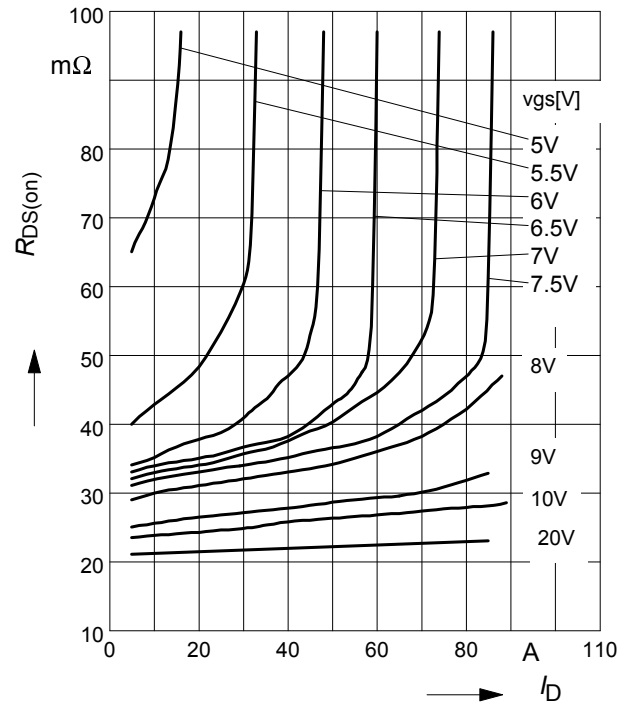
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$$R_{DS(\text{on})} = f(I_D)$$

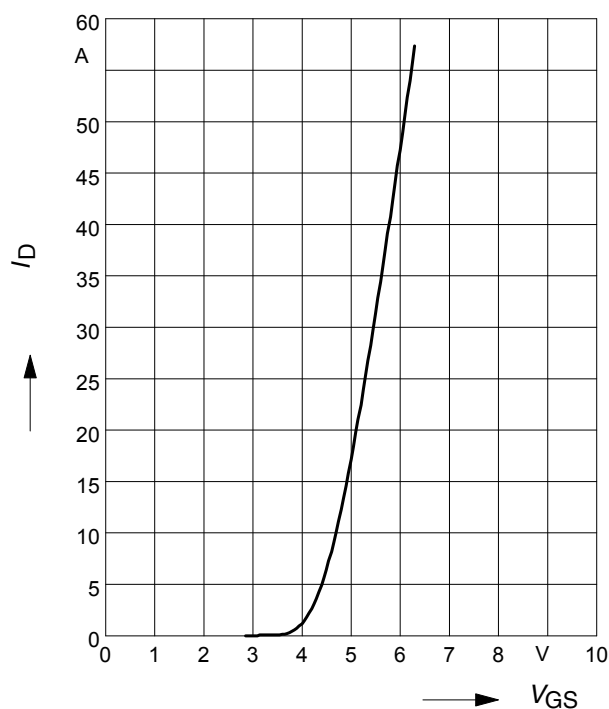
parameter: V_{GS}



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(\text{on})\text{max}}$$

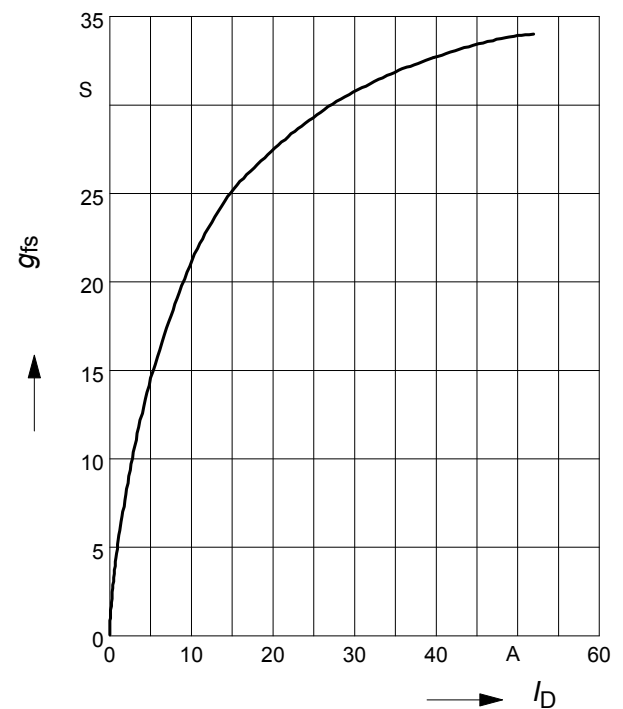
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$

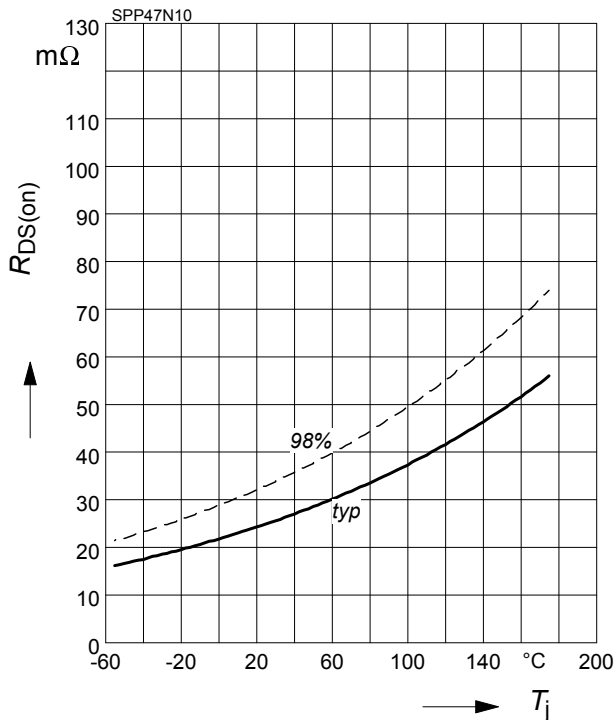
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

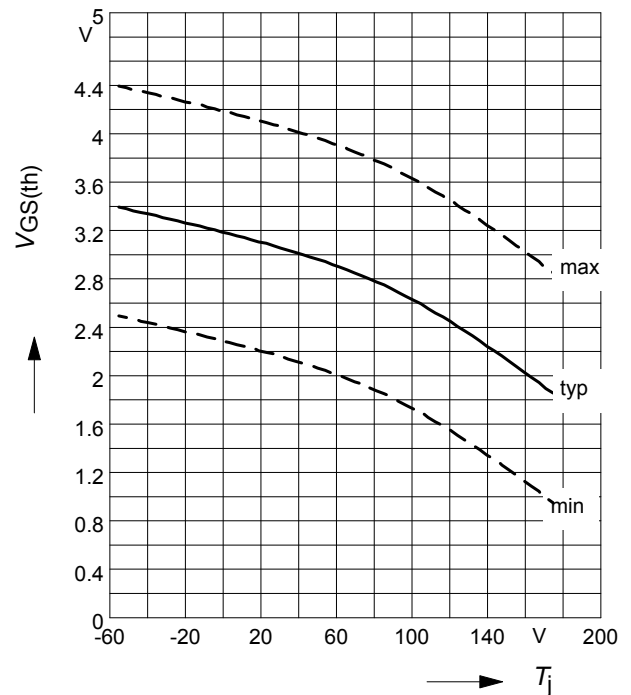
parameter: $I_D = 33\text{ A}$, $V_{GS} = 10\text{ V}$



10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

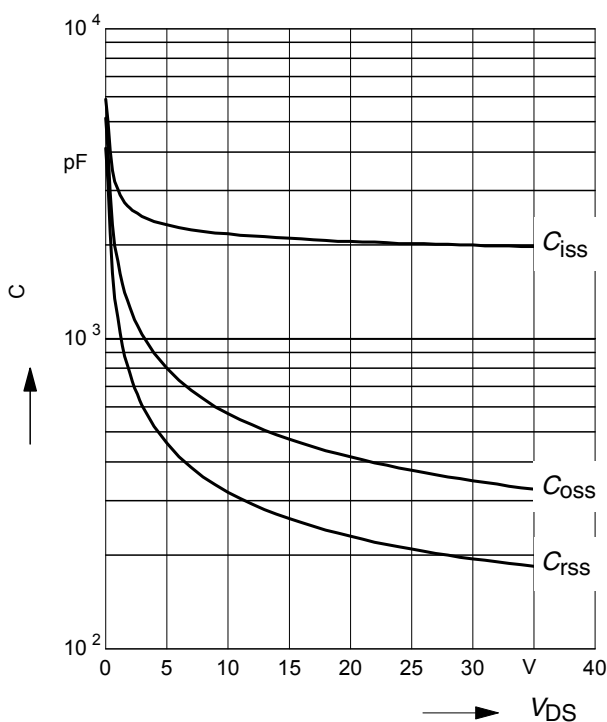
parameter: $V_{GS} = V_{DS}$, $I_D = 2\text{ mA}$



11 Typ. capacitances

$$C = f(V_{DS})$$

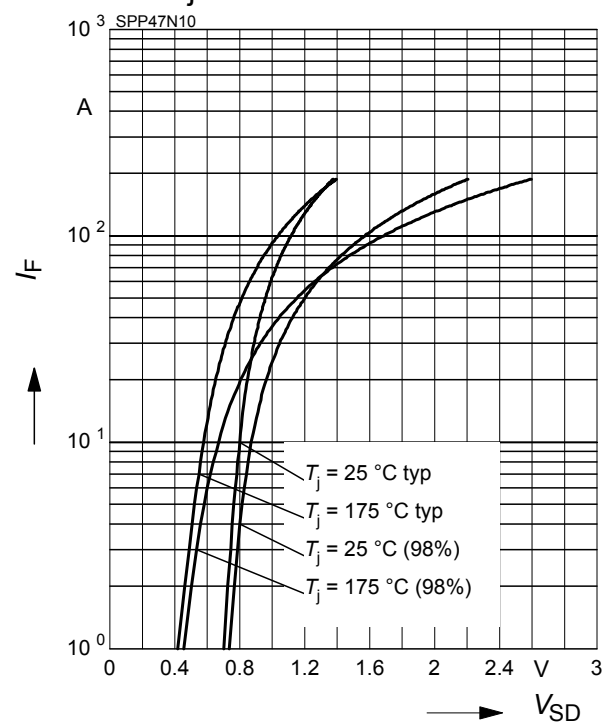
parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

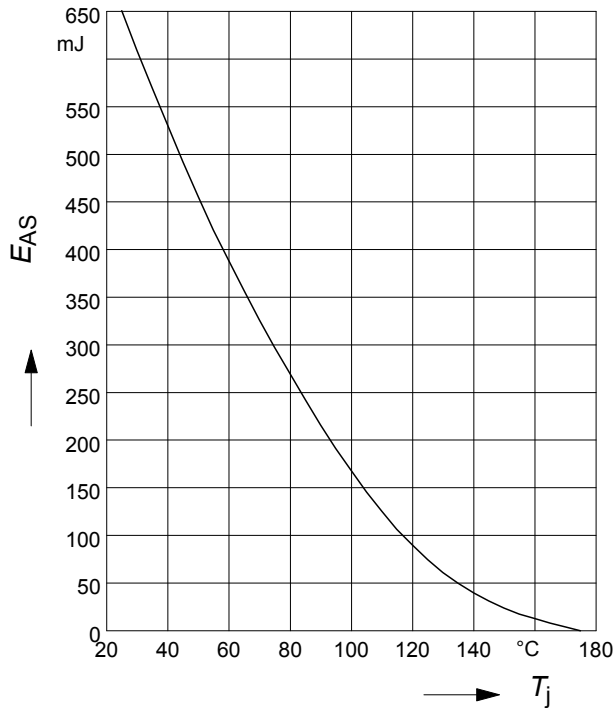
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

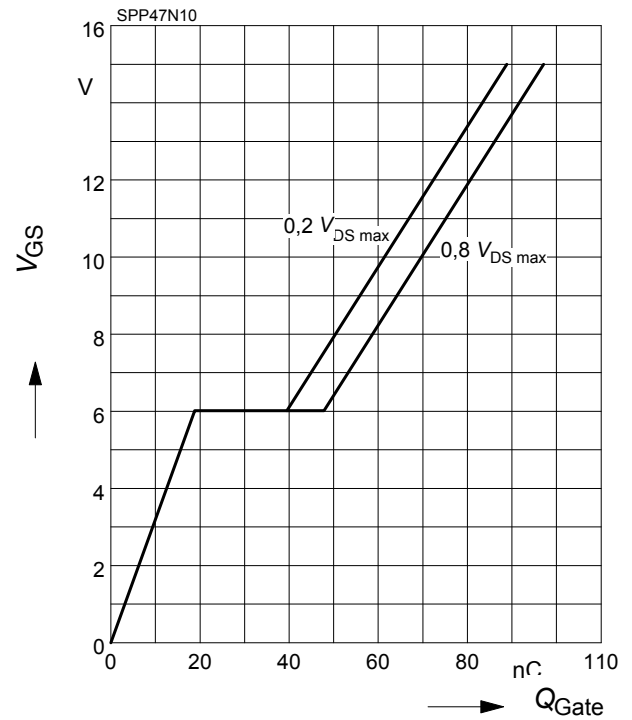
par.: $I_D = 47\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

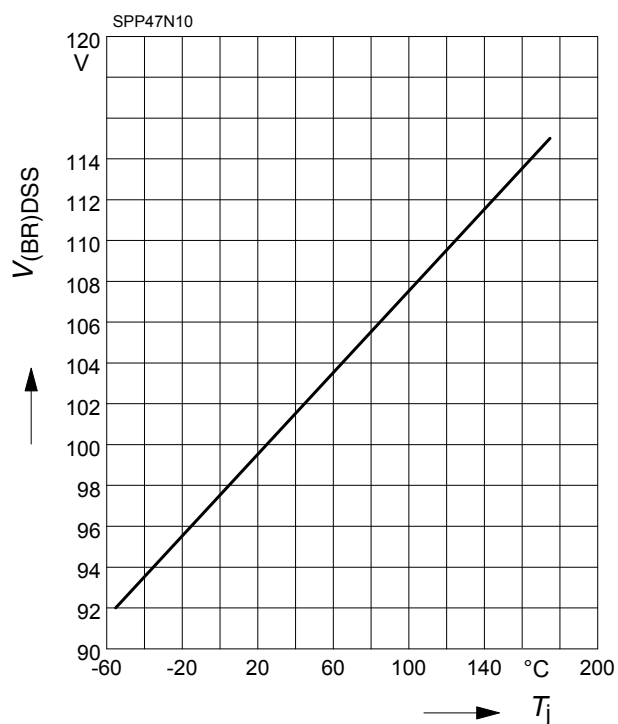
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 47\text{ A}$ pulsed



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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